







CEC6P91

-60V ▲ 83mΩ ▲ -12.5A ▲ Si MOSFET

P-channel enhancement mode
UL94V-0 rated flame retardant epoxy

DFN3x3 package ▲ MSL 3

Super high dense cell density for extremely low R_{DS(ON)} **High power and current handling capability**

MAXIMUM RATINGS

Parameter (T _c = 25°C, unless otherwise noted)	Characteristics	
Drain-Source Voltage	V _{DS}	-60V
Gate-Source Voltage	V _{GS}	±20V
Continuous Drain Current at R _{TH_JC}	I _D	-12.5A at T _C = 25°C
Continuous Drain Current at R _{TH_JA}	I _D	-4A at T _A = 25°C
Pulsed Drain Current at R _{TH_JC} Note 1	I _{DM}	-50A at T _C = 25°C
Pulsed Drain Current at R _{TH_JA} Note 1	I _{DM}	-16A at T _A = 25°C
Maximum Power Dissipation	P _D	25W at T _C = 25°C
Operating and Storage Temperature Range	T _J , T _{STG}	-55°C to +150°C

THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case Note 2	R _{TH_JC}	5°C/W
Thermal Resistance, Junction-to-Ambient Note 2	R _{TH_JA}	50°C/W

APPLICATIONS

DC/DC	DC	Load	Power	USB
Converter	Fan	Switches	Banks	Storage
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PIN DESCRIPTION

Circuit Diagram	Outline • Bottom View	Pin No.	Description
G (4) S (1,2,3)	4 3 2 1	1 2 3 4 5	Source Source Source Gate Drain



ELECTRICAL CHARACTERISTICS ▲ T_A = 25°C, unless otherwise noted

ltem	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V$, $I_D = -250\mu A$	BV_{DSS}	-60			V
Zero Gate Voltage Drain Current	$V_{DS} = -60V, V_{GS} = 0V$	I _{DSS}			-1	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 20V$, $V_{DS} = 0V$	I _{GSSF}			100	nA
Gate Body Leakage Current, Reverse	$V_{GS} = -20V, V_{DS} = 0V$	I_{GSSR}			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = -250 \mu A$	$V_{GS(th)}$	-1		-3	V
Static Drain-Source On-Resistance	V_{GS} = -10V, I_D = -1A	R _{DS(ON)}		83	100	mΩ
Static Drain-Source On-Resistance	V_{GS} = -4.5V, I_D = -1A	R _{DS(ON)}		91	120	mΩ
Dynamic Characteristics Note 4						
Input Capacitance	$V_{DS} = -30V$, $V_{GS} = 0V$, $f = 1MHz$	C _{ISS}		960		pF
Output Capacitance	$V_{DS} = -30V$, $V_{GS} = 0V$, $f = 1MHz$	Coss		70		pF
Reverse Transfer Capacitance	$V_{DS} = -30V$, $V_{GS} = 0V$, $f = 1MHz$	C _{RSS}		45		pF
Switching Characteristics Note 4						
Turn-On Delay Time	V_{DD} = -30V, V_{GS} = -10V, I_D = -1A, $R_{G(ext)}$ = 6Ω	t _{D(ON)}		11		ns
Turn-On Rise Time	V_{DD} = -30V, V_{GS} = -10V, I_D = -1A, $R_{G(ext)}$ = 6Ω	t_R		4		ns
Turn-Off Delay Time	$V_{DD} = -30V$, $V_{GS} = -10V$, $I_{D} = -1A$, $R_{G(ext)} = 6\Omega$	t _{D(OFF)}		75		ns
Turn-Off Fall Time	V_{DD} = -30V, V_{GS} = -10V, I_D = -1A, $R_{G(ext)}$ = 6Ω	t _F		14		ns
Total Gate Charge	$V_{DS} = -30V$, $V_{GS} = -4.5V$, $I_D = -3A$	Q_{G}		8.5		nC
Gate Source Charge	$V_{DS} = -30V$, $V_{GS} = -4.5V$, $I_D = -3A$	Q_{GS}		2.1		nC
Gate Drain Charge	$V_{DS} = -30V$, $V_{GS} = -4.5V$, $I_{D} = -3A$	Q_{GD}		3.3		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current		Is			-12.5	Α
Drain-Source Diode Forward Voltage Note 3	$V_{GS} = 0V$, $I_S = -1A$	V_{SD}			-1.3	V

Notes

- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2: Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3: Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4: Guaranteed by design, not subject to production testing.



REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

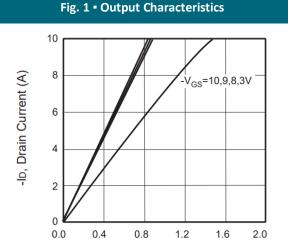


Fig. 2 • Transfer Characteristics

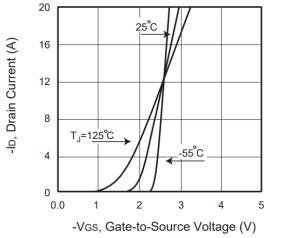


Fig. 3 - Capacitance

-VDS, Drain-to-Source Voltage (V)

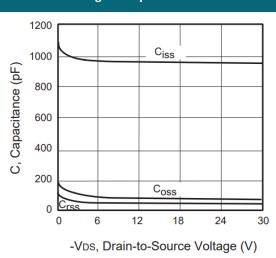


Fig. 4 • On-Resistance Variation with Temperature

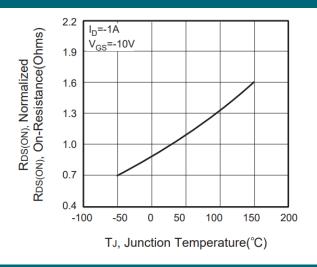


Fig. 5 • Gate Threshold Variation with Temperature

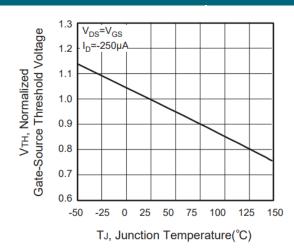
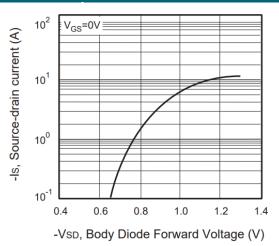


Fig. 6 • Body Diode Forward Voltage Variation with Source Current





REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

Fig. 7 • Gate Charge

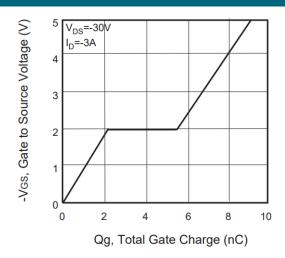


Fig. 8 • Maximum Safe Operating Area

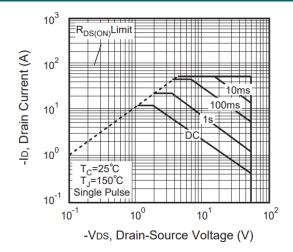


Fig. 9 • Breakdown Voltage Variation vs. Temperature

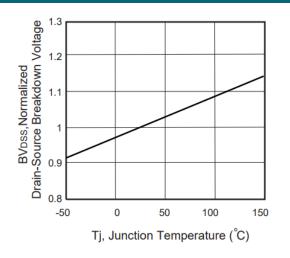
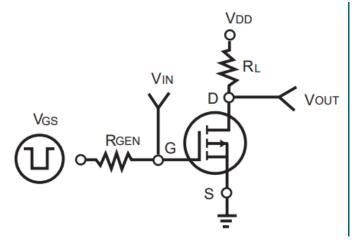
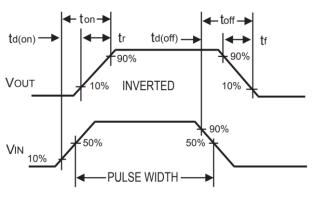


Fig. 10 • Switching Test Circuit

Fig. 11 • Switching Waveforms



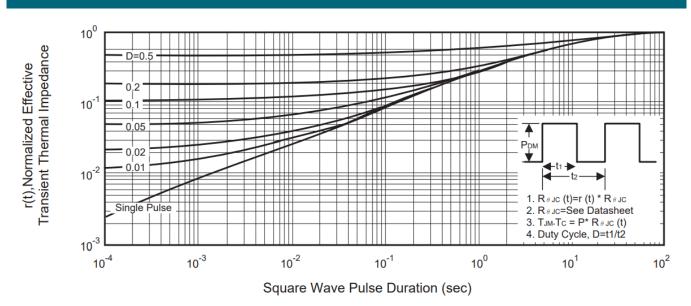


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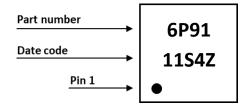


REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

Fig. 12 • Normalized Thermal Transient Impedance Curve

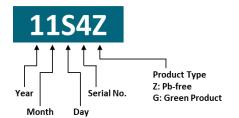


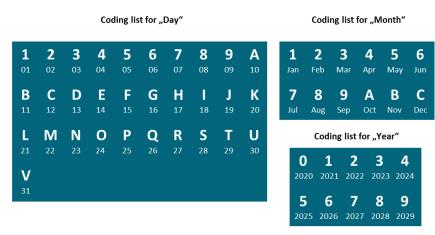
PART MARKING



DATE CODE

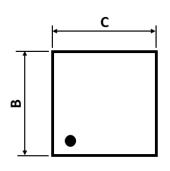
Example: 11S4Z

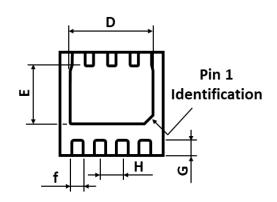


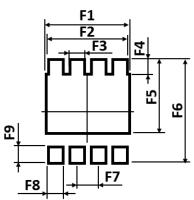


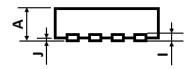


PACKAGE OUTLINE AND RECOMMENDED PAD LAYOUT









Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
Α	0.700	-	0.850
В	2.900	-	3.100
С	2.900	-	3.100
D	2.350	-	2.490
Е	1.650	-	1.750

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
f	0.300	-	0.400
G	0.350	-	0.480
Н		0.650 (BSC)	
1		0.203 (REF)	
J	0.000	-	0.050

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	2.500	-
F2	-	2.400	-
F3	-	0.450	-
F4	-	0.450	-
F5	-	2.200	-

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F6	-	3.100	-
F7	-	0.650	-
F8	-	0.450	-
F9	-	0.500	-

Notes: 1. The suggested land pattern dimensions have been provided for reference only.

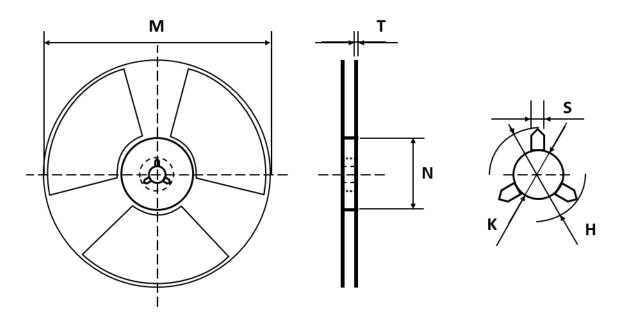
2. For further information, please reference document IPC-7351A.

ORDERING INFORMATION

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CEC6P91	DFN 3x3	Reel	3,000pcs	6,000pcs	48,000pcs

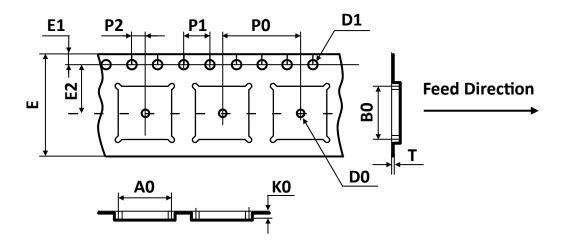


REEL DIMENSIONS ▲ All dimensions in mm



Tape Size	Reel Size	M	N	T	Н	К	S
12mm	Ø330	Ø330.00	Ø100.00	2.20	20.00	13.20	3.00
	<i>9</i> 330	±2.00	±0.50	±0.20	±1.00	±0.20	±1.00

TAPE DIMENSIONS ▲ All dimensions in mm

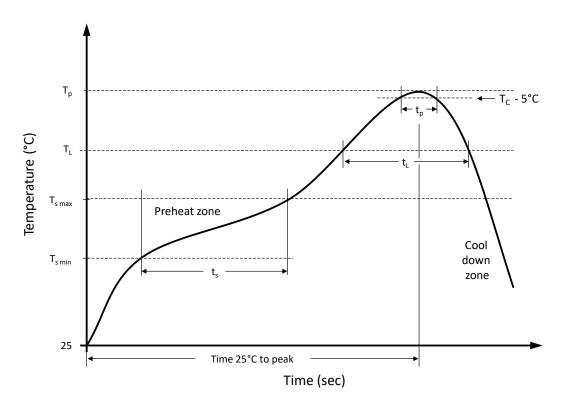


Package	Α0	В0	КО	D0	D1	E	E1	E2	Р0	P1	P2	T
DFN 3x3	3.30	3.30	1.10	1.50	1.50	12.00	1.75	5.50	8.00	4.00	2.00	0.23
DFN 5X5	±0.10	±0.10	±0.15	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05	±0.02

Note: All dimensions meet EIA-481-D requirements.



RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{s min}$	100 °C	150 °C
Preheat temperature max.	T _{s max}	150 °C	200 °C
Preheat time t _s from T _{s min} to T _{s max}	ts	120 seconds	120 seconds
Ramp-up rate (T₁ to Tp)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	T_L	183 °C	217 °C
Time t _L maintained above T _L	t _L	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t _p	20 seconds max.	30 seconds max.
Ramp-down rate (T _L to T _p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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